

Title (en)

FABRICATING AN MTJ WITH LOW AREAL RESISTANCE

Title (de)

FABIKATION EINES MTJ MIT NIEDRIGEM FLÄCHENWIDERSTAND

Title (fr)

PRODUCTION D'UNE JONCTION MAGNETIQUE A EFFET TUNNEL A FAIBLE RESISTANCE SURFACIQUE

Publication

EP 1038325 A1 20000927 (EN)

Application

EP 99934121 A 19990715

Priority

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- US 11932698 A 19980720

Abstract (en)

[origin: WO0004592A1] A method of fabricating a magnetoresistive tunnel junction including forming a thin, continuous layer of aluminum alloy (15) on the surface of a first magnetic layer (11), the continuous layer of aluminum alloy including greater than 90 % aluminum and traces of materials having atoms that are different from the atoms of the aluminum to produce grains which are smaller than grains of pure aluminum. The continuous layer (16) of aluminum alloy is oxidized, nitridized, or both to produce a continuous layer of non-conductive material and a second magnetic layer (18) is formed on the layer of non-conductive material.

IPC 1-7

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IPC 8 full level

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CPC (source: EP KR US)

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